

Description

The PSJMDP65R650 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

MOSFET Product Summary

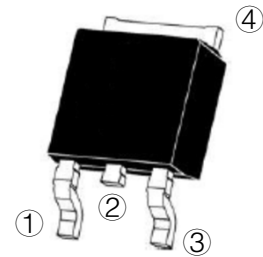
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
650	510@ $V_{GS} = 10V$	7.0

Feature

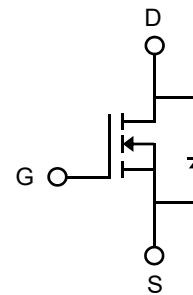
- Fast Switching Capability
- Lead free product is acquired.
- Avalanche Energy Tested

Applications

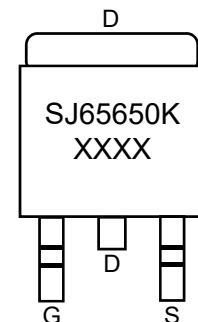
- PWM applications
- Load Switch
- Power Management
- DC-DC Converters



TO-252 (Top View)



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current-Continuous ¹⁾	I_D	$T_C=25^\circ C$	7.0
		$T_C=100^\circ C$	5.3
Pulsed Drain Current ²⁾	I_{DM}	10	A
Total Power Dissipation ³⁾	P_D	80.6	W
Avalanche Current ⁴⁾	I_{AS}	4.5	A
Avalanche Energy ⁴⁾	E_{AS}	199.5	mJ
Thermal Resistance , Junction-to-Case ⁵⁾	$R_{\theta JC}$	1.5	$^\circ C/W$
Thermal Resistance , Junction-to-Ambient ⁶⁾	$R_{\theta JA}$	47.5	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	2.9	3.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1A$	-	510	650	m Ω
Dynamic Characteristics⁷⁾						
Input Capacitance	C_{iss}	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	-	334.3	-	pF
Output Capacitance	C_{oss}		-	16.2	-	
Reverse Transfer Capacitance	C_{rss}		-	0.9	-	
Switching Characteristics⁷⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 400V, V_{GS} = 10V,$ $I_D = 1A, R_G = 10\Omega$	-	26.4	-	ns
Turn-on Rise Time	t_r		-	11.4	-	
Turn-Off Delay Time	$t_{d(off)}$		-	132.1	-	
Turn-Off Fall Time	t_f		-	38.1	-	
Total Gate Charge	Q_g	$V_{DS} = 480V, V_{GS} = 10V,$ $I_D = 1A$	-	6.1	-	nC
Gate-Source Charge	Q_{gs}		-	1.4	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Gate Resistance	R_g	$f=1MHz$, Open Drain	-	106.8	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$	-	0.8	1.3	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 1A, V_R = 200V,$ $dI_F/dt = 100A/\mu s$	-	100.6	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	419.7	-	μC
Peak Reverse Recovery Current	I_{rrm}		-	8.4	-	A

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J_Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 10\mu s$, Duty Cycle $\leq 1\%$.
4. This single-pulse measurement was taken under the following condition [$L=20mH, V_{GS}=10V, V_{DS}=100V$]while it's value is limited by $T_{J_Max}=150^\circ C$.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on infinite heatsink.
7. Guaranteed by design, not subject to production.

Typical Characteristics

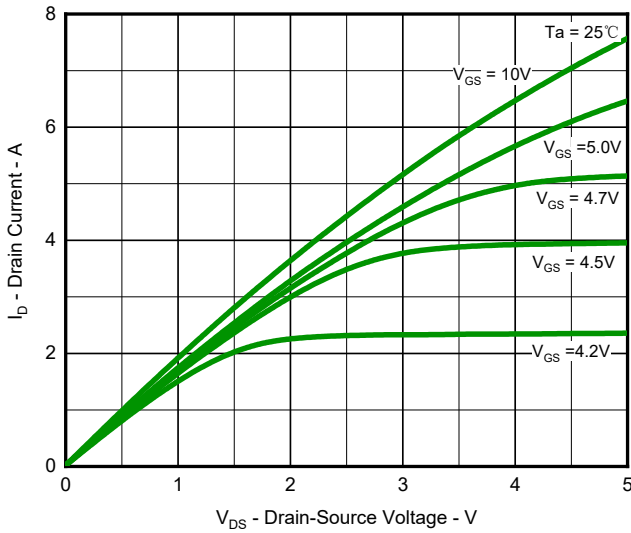


Fig.1 Output Characteristics

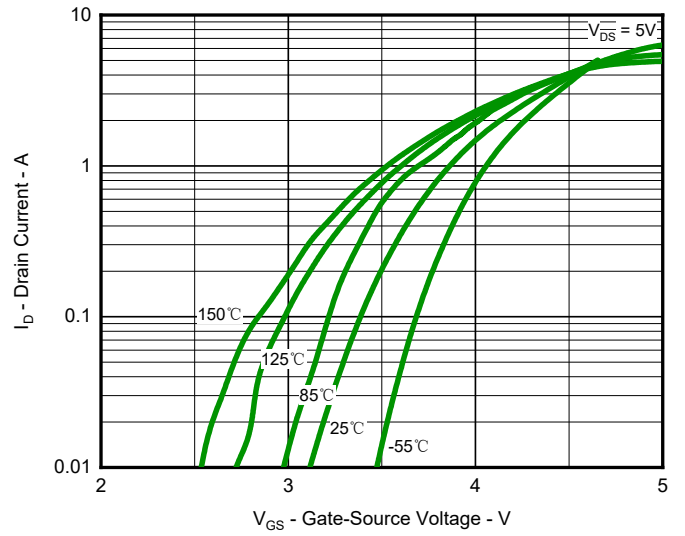


Fig.2 Typical Transfer Characteristic

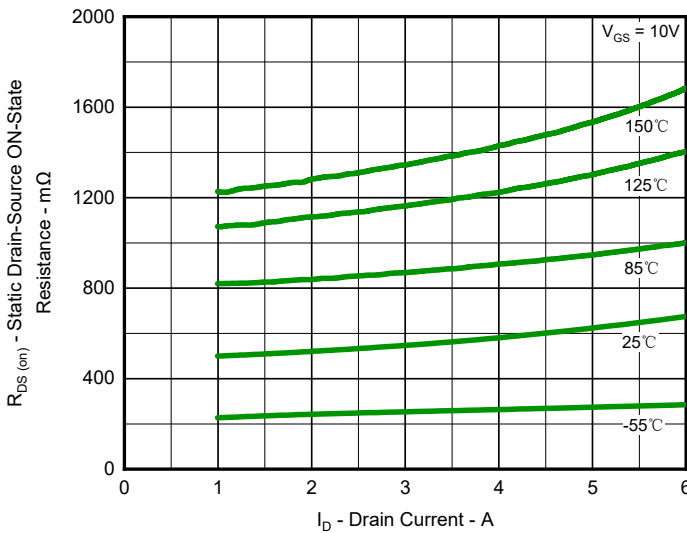


Fig.3 Typical On-Resistance vs Drain Current and Temperature

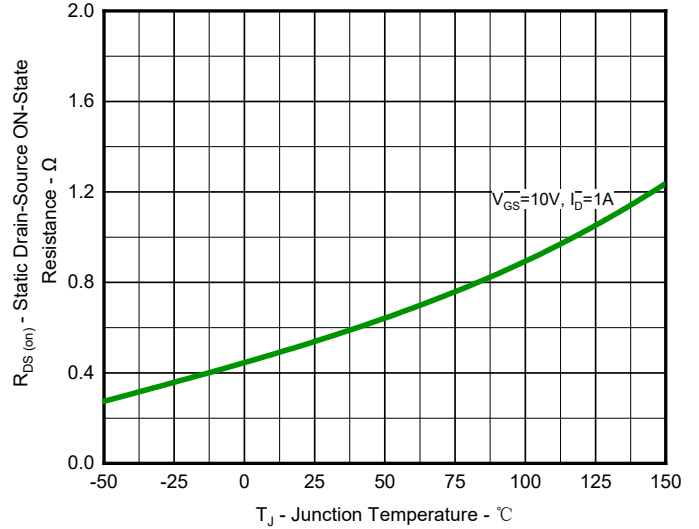


Fig.4 On-Resistance Variation with Temperature

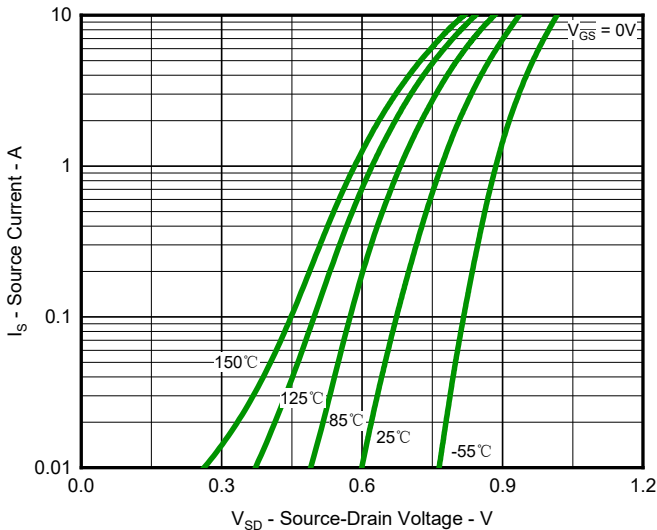


Fig.5 Diode Forward Voltage vs. Current

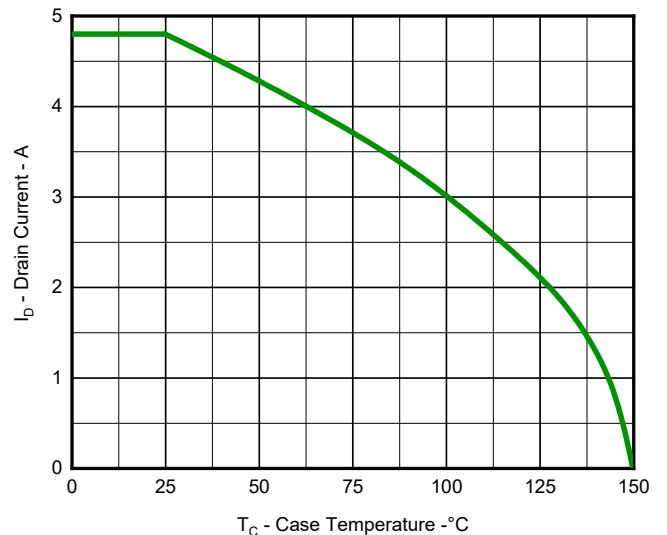


Fig.6 Maximum Drain Current vs. Case Temperature

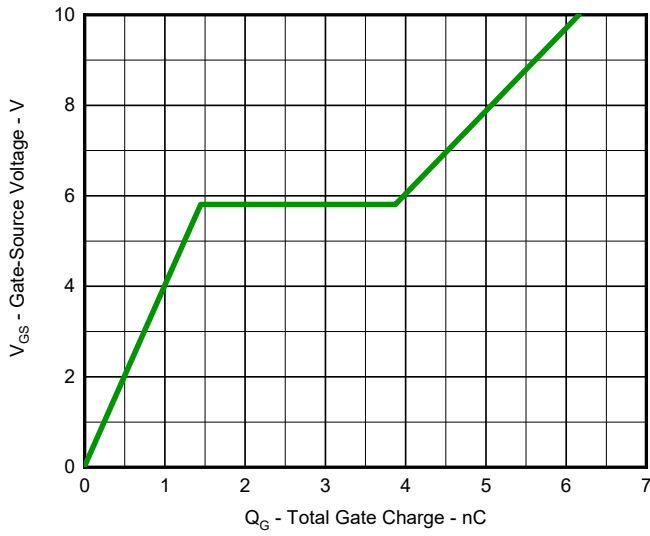


Fig.7 Gate Charge Characteristics

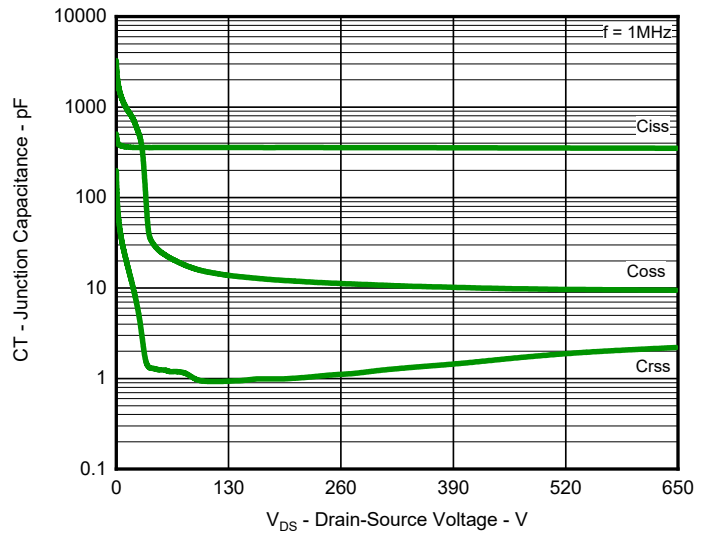


Fig.8 Typical Junction Capacitance

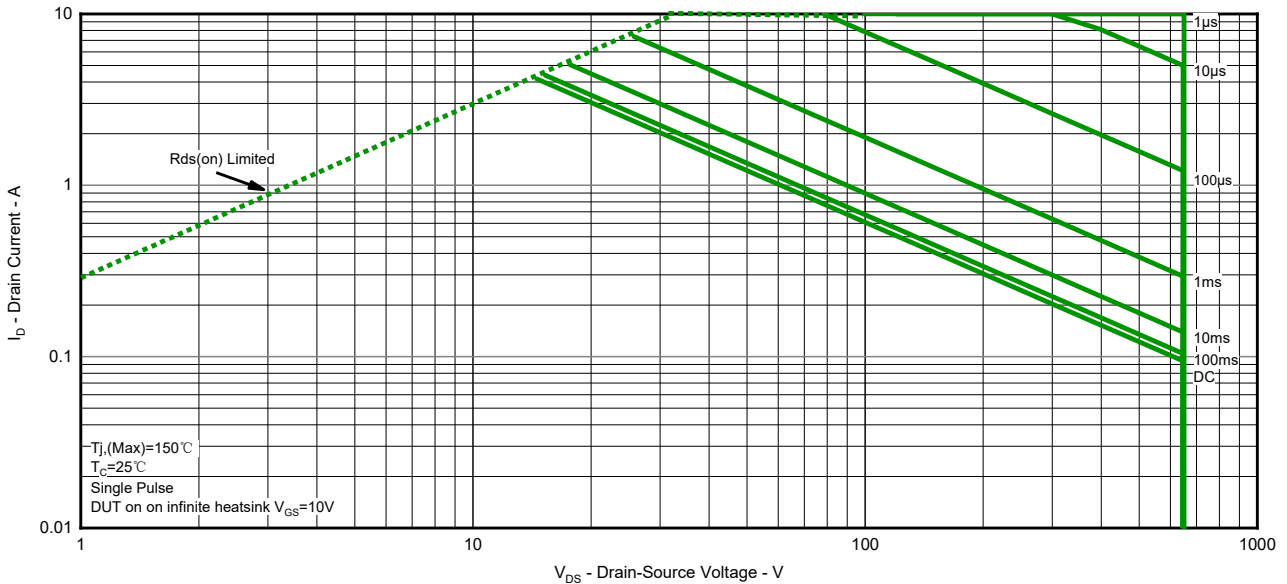


Fig.9 Safe Operation Area

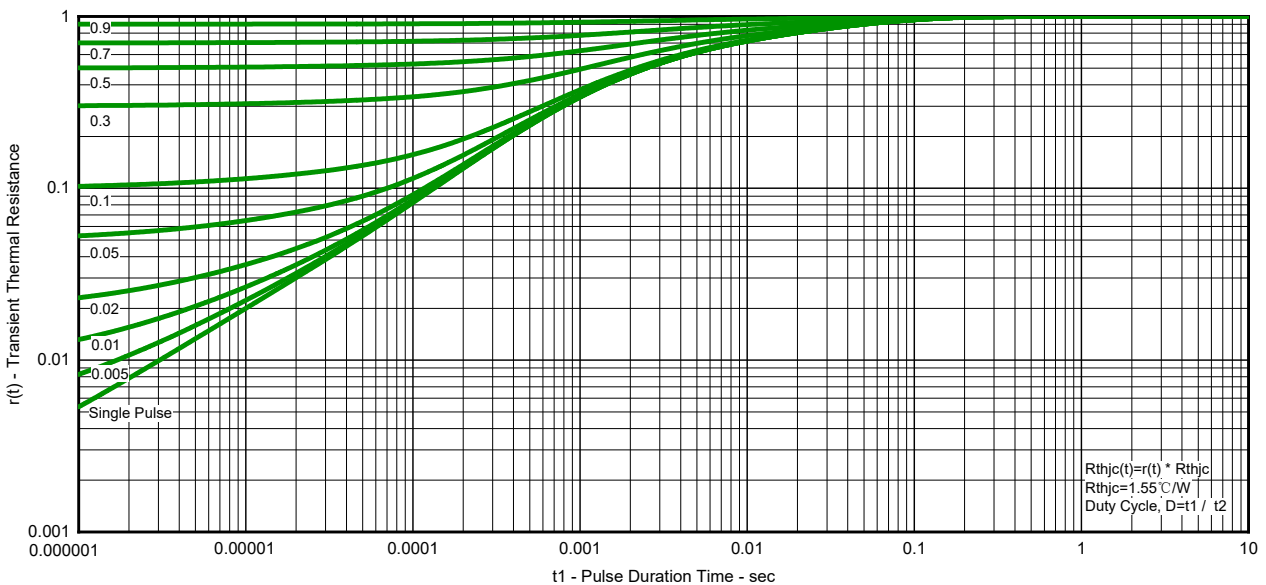
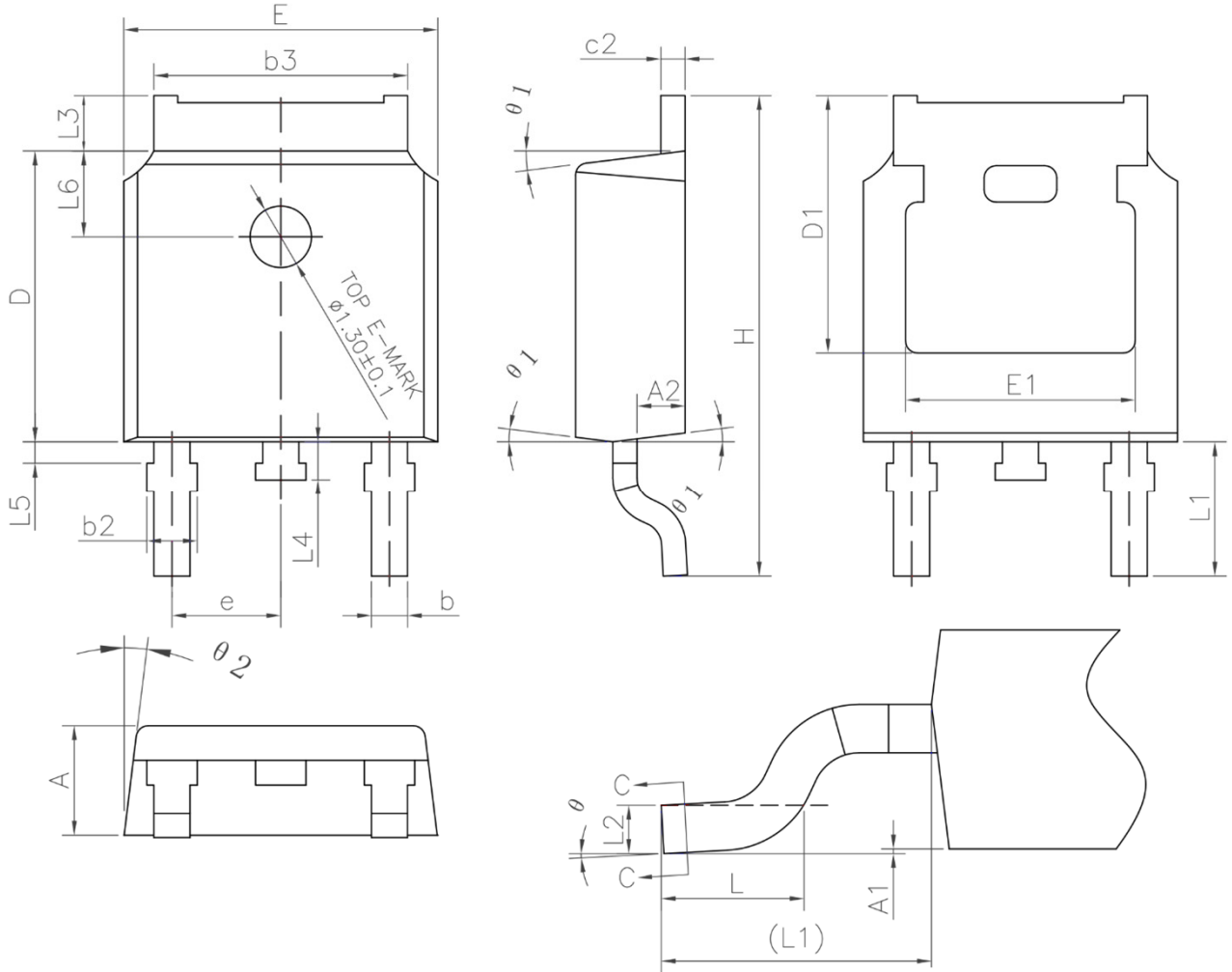


Fig.10 Transient Thermal Resistance

Product Dimension (TO-252)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	2.20	2.38	0.087	0.094	e	2.186	2.386	0.086	0.094
A1	0.00	0.10	0.000	0.004	H	9.80	10.40	0.386	0.409
A2	0.90	1.10	0.035	0.043	L	1.40	1.70	0.055	0.067
b	0.72	0.82	0.028	0.032	L1	2.90 Ref.		0.114 Ref.	
b2	0.72	0.90	0.028	0.035	L2	0.508 BSC.		0.020 BSC.	
b3	5.13	5.46	0.202	0.215	L3	0.90	1.25	0.035	0.049
c	0.47	0.60	0.019	0.024	L4	0.60	1.00	0.024	0.039
c2	0.47	0.60	0.019	0.024	L5	0.15	0.75	0.006	0.030
D	6.00	6.20	0.236	0.244	L6	1.80 Ref.		0.071 Ref.	
D1	5.25	-	0.207	-	θ	0°	8°	0°	8°
E	6.50	6.70	0.256	0.264	θ_1	5°	9°	5°	9°
E1	4.70	-	0.185	-	θ_2	5°	9°	5°	9°

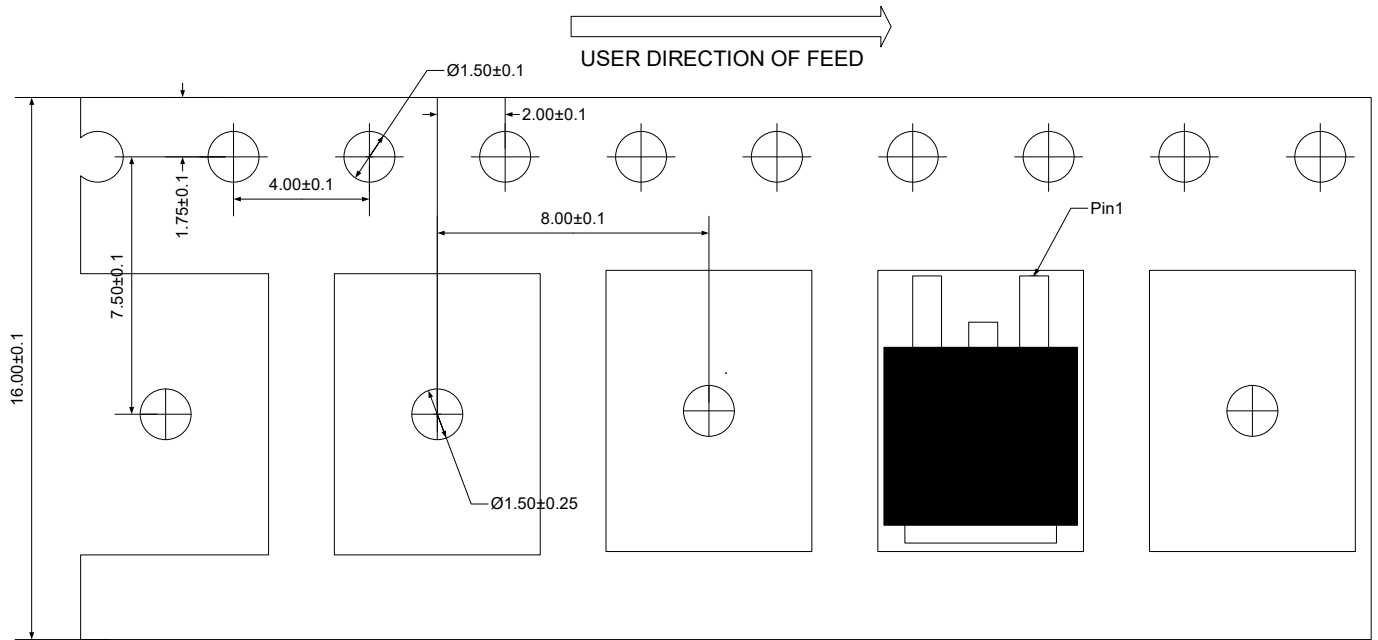
N-Channel MOSFET

PSJMDP65R650

Ordering Information

Device	Package	Reel	Shipping
PSJMDP65R650	TO-252	13"	2500 / Tape & Reel

Load With Information



Unit:mm

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